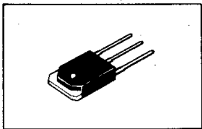




No.1269

# 2SD1402



NPN Triple Diffused Planar Type Silicon Transistor  
FOR CTV HORIZONTAL DEFLECTION OUTPUT

**Features:**

- High breakdown voltage and high reliability
- High switching speed
- Capable of being mounted easily due to one-point fixing type plastic mold package

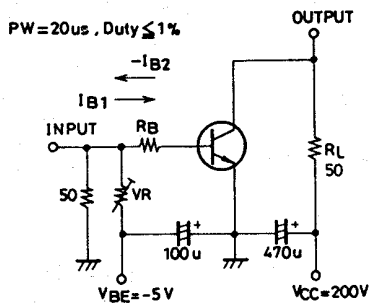
**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	1500	V
Collector to Emitter Voltage	V <sub>CEO</sub>	800	V
Emitter to Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	I <sub>C</sub>	5	A
Peak Collector Current	i <sub>cp</sub>	16	A
Collector Dissipation	P <sub>C</sub>	T <sub>C</sub> =25°C 120	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta=25°C**

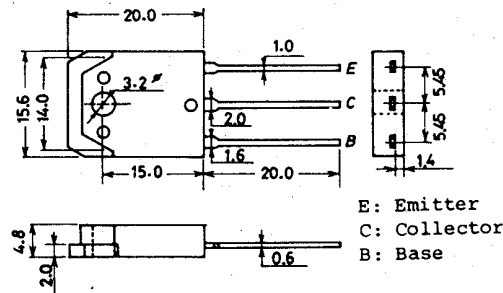
			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	uA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			1	mA
DC Current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	8			
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1A		3		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			5	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			1.5	V
C-B Breakdown Voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> =5mA, I <sub>E</sub> =0	1500			V
C-E Breakdown Voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =100mA, R <sub>BE</sub> =∞	800			V
E-B Breakdown Voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> =200mA, I <sub>C</sub> =0		7		V
Fall Time	t <sub>f</sub>	I <sub>C</sub> =4A, I <sub>B1</sub> =0.8A, I <sub>B2</sub> =-1.6A			0.7	us

**Switching Time Test Circuit**



**Case Outline 2022**

(unit:mm)



These specifications are subject to change without notice.

TOKYO SANYO ELECTRIC CO., LTD. SEMICONDUCTOR DIVISION  
15-13, 6-CHOME, SOTOKANDA, CHIYODA-KU, TOKYO 101 JAPAN